

Correction

Low-Temperature Formed Quaternary NiZrSiGe Nanocrystal Memory [Int. J. Electrochem. Sci., 10 (2015) 6500-6508]

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The authors regret that there was error in the original published version.

The affiliations of the author *Huei Yu Huang* were not assigned correctly in the paper and the affiliations should be added “School of Dentistry, College of Oral Medicine, Taipei Medical University, Taipei, Taiwan”.

This was not noticed at the time by the authors and it is corrected by this correction now, and we apologize for any inconvenience this may cause.

The correct paragraph is as follows:

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